L Number	Hits	Search Text	DB	Time stamp
1	2	4972251.pn.	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 10:31
2	528	(438/108).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 10:31
3	3	((438/108).CCLS.) and protective with film with surface with (chip IC die semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 10:33
4	801	(438/$).ccls. and protective with film with surface with (chip IC die semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 10:34
5	34	((438/$).ccls. and protective with film with surface with (chip IC die semiconductor)) and flip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:29
6	1256	(257/692).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:29
7	14	((257/692).CCLS.) and passivation and flip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:30
8	41	((257/692).CCLS.) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:30
9	193	((257/692).CCLS.) and insulating with layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:30
10	667	(257/$).ccls. and passivation and flip	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:31
11	249	((257/$).ccls. and passivation and flip) and passivation with pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 11:31
-	2682	Continuation with PCT	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 12:03
-	18	(Continuation with PCT) and Continuation with PCT and (257/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 12:16
-	2	5470787.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 14:55

-	472	(passivation with layer with made) and (438/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 14:57
-	50	((passivation with layer with made) and (438/$).ccls.) and solder with bump	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:07
-	40	5736456.URPN.	USPAT	2002/08/19 14:59
-	521	passivation with layer with (silicon adj nitride silicon oxide MgO) and bump	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:14
-	222	(passivation with layer with (silicon adj nitride silicon oxide MgO) and bump) and (257/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:15
-	252	passivation with layer with (silicon adj nitride silicon adj oxide MgO) and bump	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:15
-	109	(passivation with layer with (silicon adj nitride silicon adj oxide MgO) and bump) and (257/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:25
-	5	("4434434" | "5268072" | "5629564" | "5785236" | "5795819").PN.	USPAT	2002/08/19 15:21
-	90	passivation with layer with thermal with expansion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:44
-	22218	silicon with germanium dioxide with layer with thermal with coefficient	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:52
-	151	(silicon with germanium dioxide with layer with thermal with coefficient) and passivation with layer and bump	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:50
-	3	silicon with germanium with dioxide with layer with thermal with coefficient	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:53
-	479795	silicon with dioxide with coefficient with thermal expansion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:57
-	9020	(silicon with dioxide with coefficient with thermal expansion) and (257/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:58
-	1751	((silicon with dioxide with coefficient with thermal expansion) and (257/$).ccls.) and bump	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:56

–	325	(((silicon with dioxide with coefficient with thermal expansion) and (257/$).ccls.) and bump) and passivation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:56
–	243	(((silicon with dioxide with coefficient with thermal expansion) and (257/$).ccls.) and bump) and passivation	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 15:56
–	277	silicon with dioxide with coefficient with thermal with expansion	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 16:03
–	72	(silicon with dioxide with coefficient with thermal with expansion) and (257/$).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 16:00
–	0	silicon adj dioxide with "coefficient of thermal expansion"	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 16:04
–	116	silicon adj dioxide with "thermal expansion coefficient"	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 16:13
–	20673	silicon with germanium dioxide with "thermal expansion coefficient"	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 16:14
–	3	silicon with germanium with dioxide with "thermal expansion coefficient"	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 16:21
–	7	silicon with germanium with dioxide with "thermal expansion"	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 16:27
–	4	(silicon with germanium with dioxide with "thermal expansion") not (silicon with germanium with dioxide with "thermal expansion coefficient")	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/19 16:22
–	9	silicon with germanium with oxide with "thermal expansion"	USPAT; EPO; JPO; DERWENT; IBM_TDB	2002/08/20 09:42
–	1	silicon with germanium with oxide with "thermal expansion"	US-PGPUB	2002/08/19 16:31